

Supporting Information

Effects of interface adsorption configurations on dye-sensitized solar cell performance at the stoichiometric and defected TiO₂ anatase (101): a theoretical investigation

Guang Yang,^a Guomin Sui,^a Yuxia Liang,^a and Xiaodong Xue,^a Yaqing Feng^{*ab} and Bao Zhang^{*a}

^a *School of Chemical Engineering and Technology, Tianjin University, Tianjin 300350, PR China*

^b *Tianjin Co-Innovation Center of Chemical Science and Engineering, Tianjin University, Tianjin 300072, PR China*

Email: baozhang@tju.edu.cn

S1. Computational Results

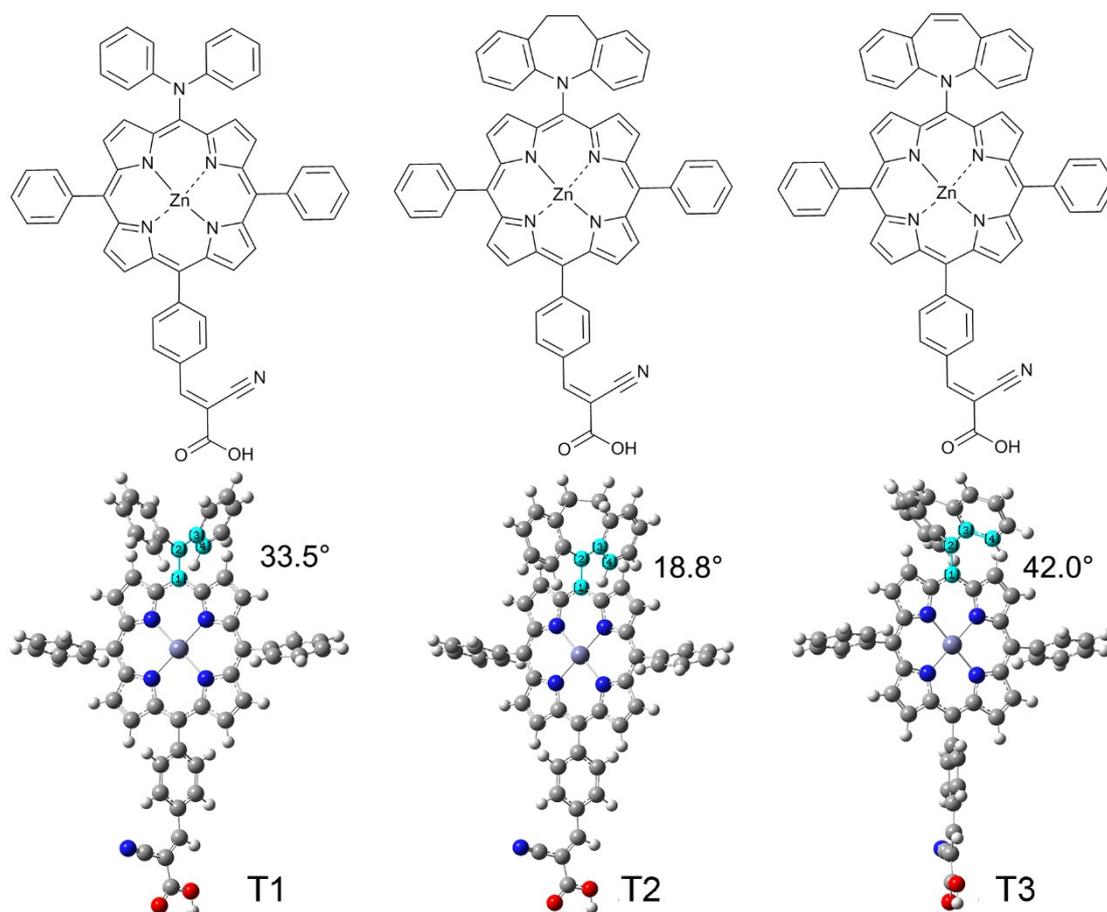


Figure S1. Molecular structures and optimized geometry of ground states of T1-3, with the values showing the dihedral angles of atoms in green.

Table S1. Calculated adsorption configurations of T1-3 and their adsorption energies in three adsorption configurations (D_{NO} , D_N and D_O) on the defected anatase TiO₂ (101) surfaces.

Dye	Configurations	Adsorption Energy (eV)	Figures
T1	D_{NO} (O_{2c-vac} , N-Ti _{5c} , O-Ti _{5c})	-1.79	Fig S1 a
	D_N (O_{2c-vac} , N-Ti _{5c})	-1.72	Fig S1 b
	D_O (O_{2c-vac} , O-Ti _{5c})	-1.47	Fig S1 b
T2	D_{NO} (O_{2c-vac} , N-Ti _{5c} , O-Ti _{5c})	-1.77	Fig S1 d
	D_N (O_{2c-vac} , N-Ti _{5c})	-1.71	Fig S1 e
	D_O (O_{2c-vac} , O-Ti _{5c})	-1.44	Fig S1 f
T3	D_{NO} (O_{2c-vac} , N-Ti _{5c} , O-Ti _{5c})	-1.76	Fig S1 g
	D_N (O_{2c-vac} , N-Ti _{5c})	-1.75	Fig S1 h
	D_O (O_{2c-vac} , O-Ti _{5c})	-1.26	Fig S1 i

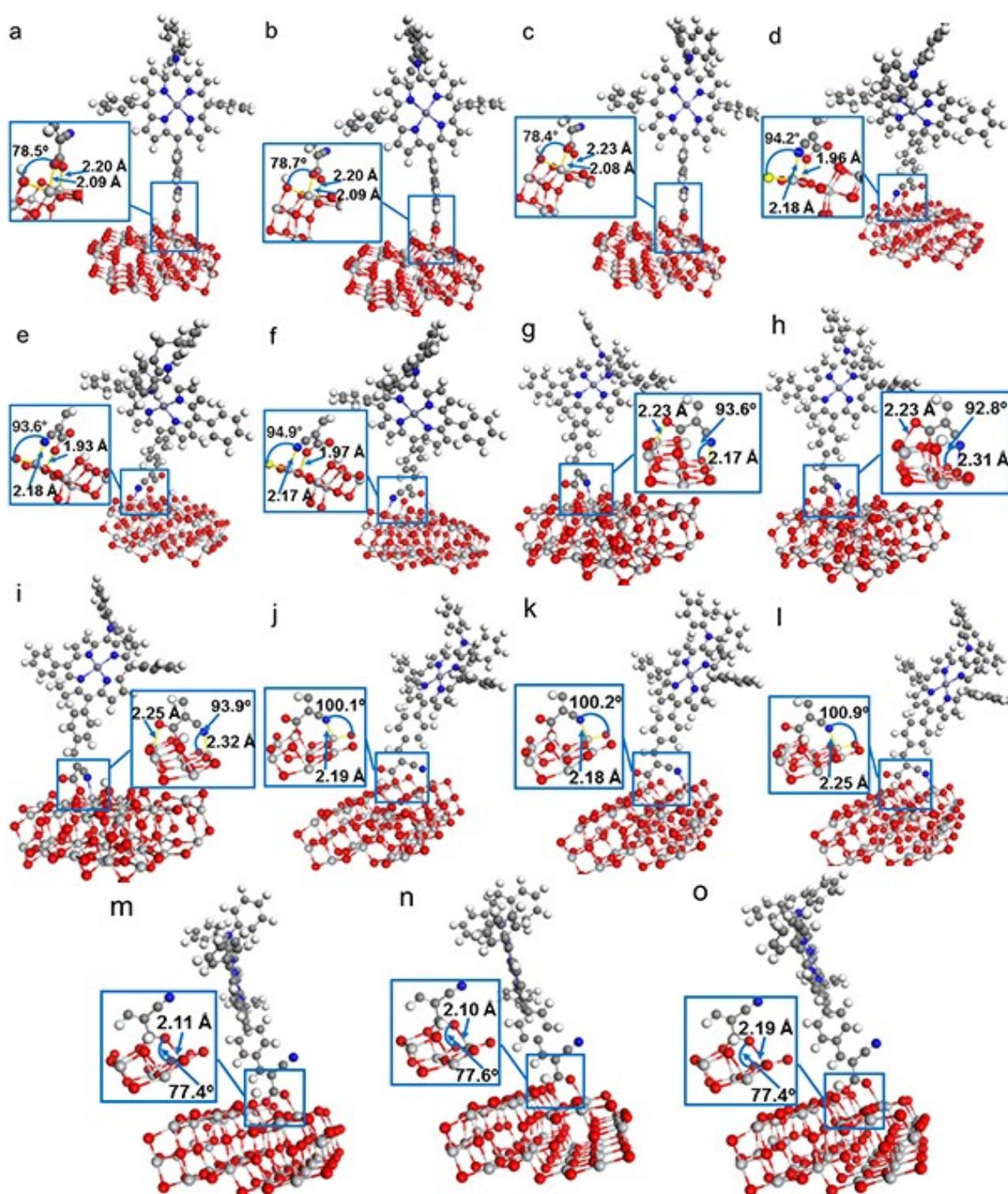


Figure S2. Optimized adsorption configurations of dye T1-3 on the ideal and defected surface. Black, white, red, blue, gray and purple represent C, H, O, N, Ti and Zn atoms respectively. a - c represent the BB mode for T1-3; d - f represent the T mode for T1-3; g - i represent the configurations (D_{NO}) with one O atom in the O_{2c} vacancy and the N and another O atoms at neighboring Ti_{5c} atoms, with the N-Ti distance of 2.31 - 2.32 Å; j - l show the configurations (D_N) with O and N atoms in vacancy and at neighboring T_{5c} atom, with N-Ti distance of 2.18 - 2.25 Å;

m - o present the configurations (D_0) with O-Ti_{5c} bonds of 2.10 – 2.19 Å.

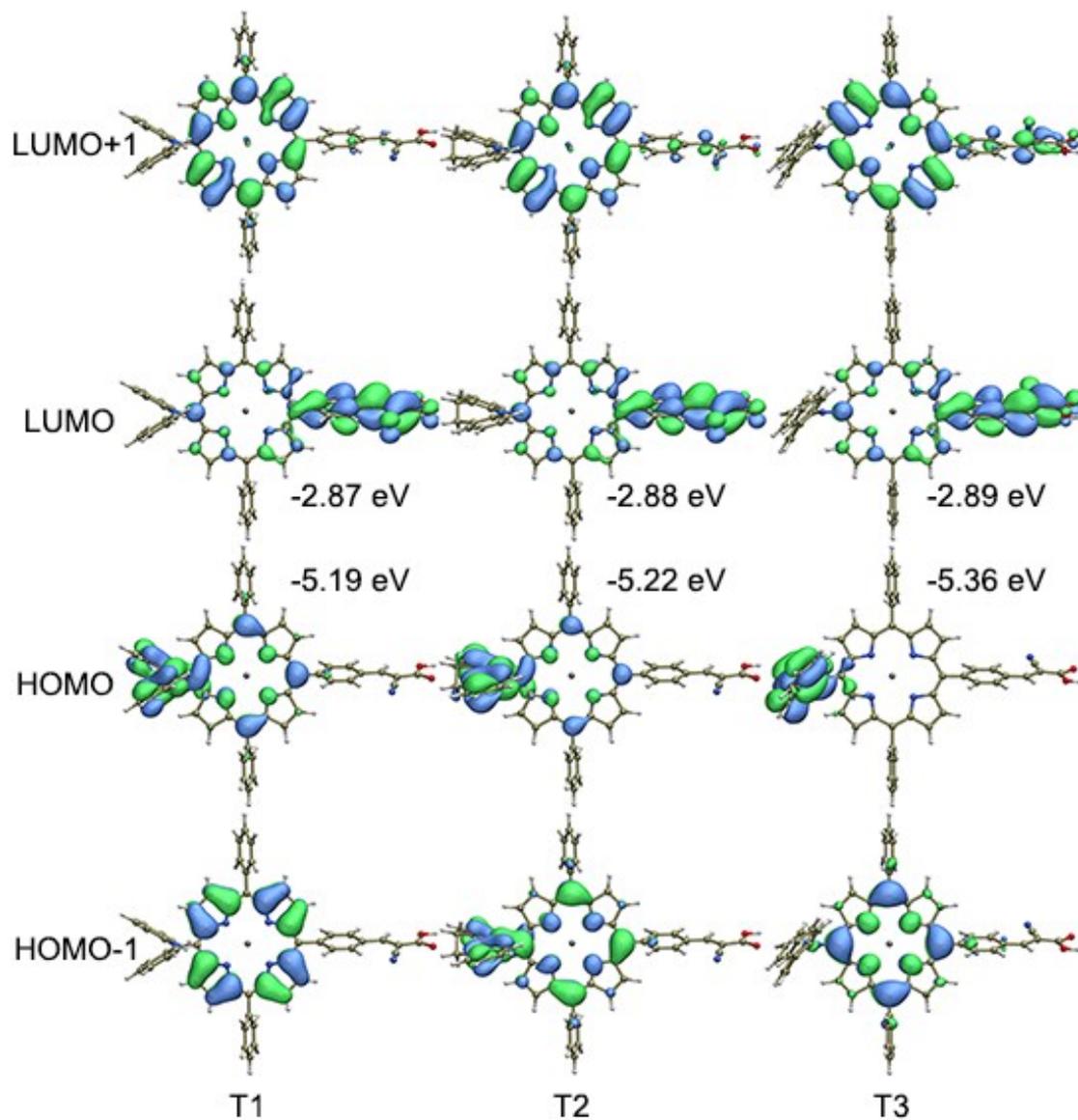


Figure S3. Calculated isosurfaces of the HOMO-1 to LUMO+1 and energy levels of HOMO and LUMO for T1-3.

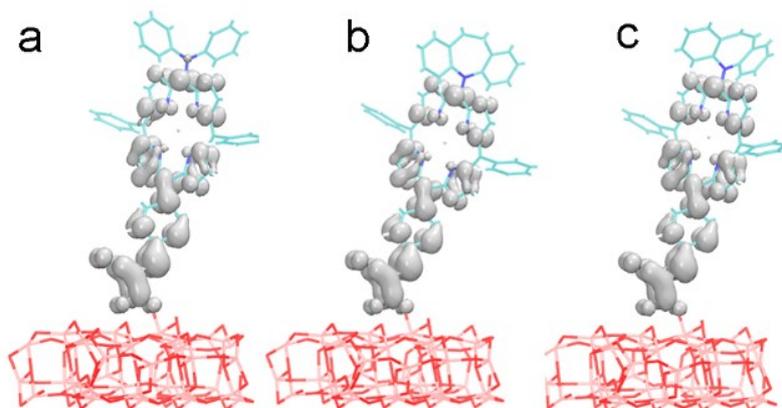


Figure S4. Calculated EH orbitals LUMO for T1-3.

Table S2. Adsorption energy (E_{ads} , eV), of Dye/TiO₂ systems for T1-3 with different adsorption configurations in reduced TiO₂ surface..

Dye	Adsorption Configuration	Adsorption Energy (E_{ads} , eV)
T1	D _{NO}	-1.79
	D _N	-1.72
	D _O	-1.47
T2	D _{NO}	-1.77
	D _N	-1.71
	D _O	-1.44
T3	D _{NO}	-1.76
	D _N	-1.70
	D _O	-1.26

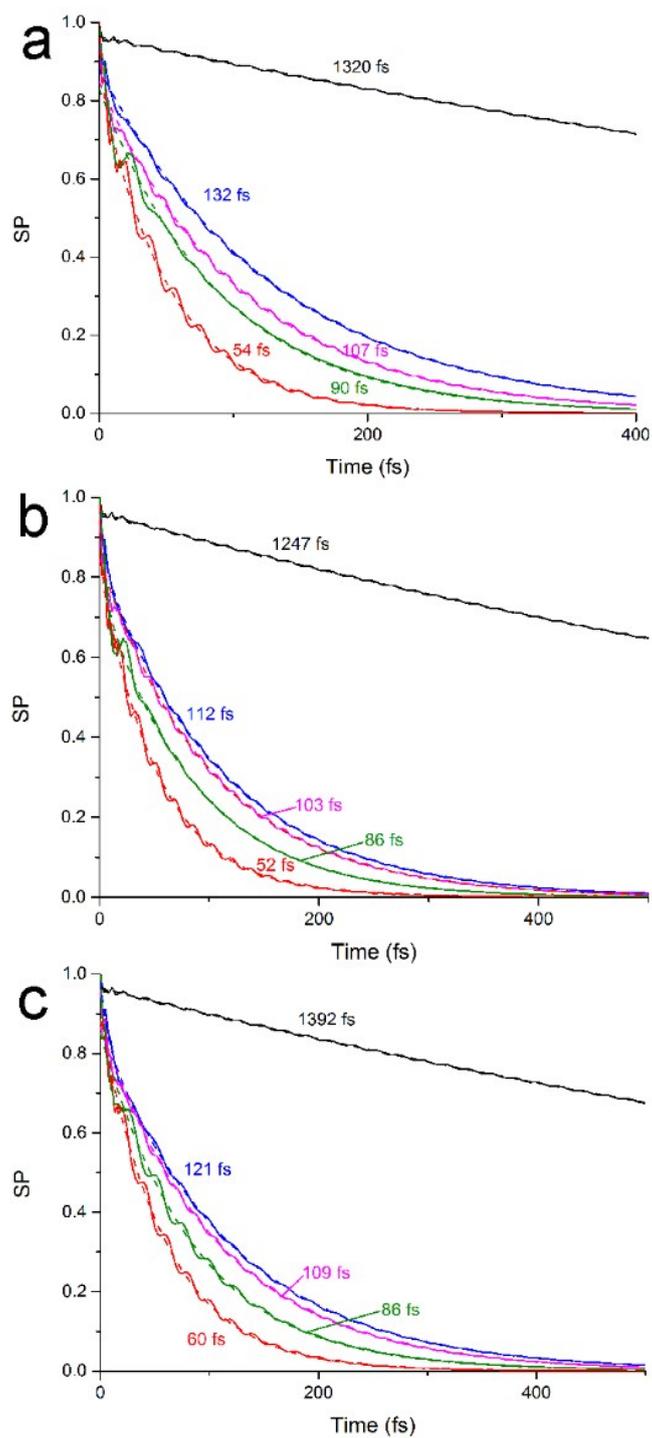


Figure S5. the IET curves (solid line) and exponential fitting (dashed line) from LUMOs orbital of T1 (a), T2 (b) and T3 (c) in adsorption configurations BB (black), D_{NO} (blue), D_N (magenta), D_O (green) and T (red).

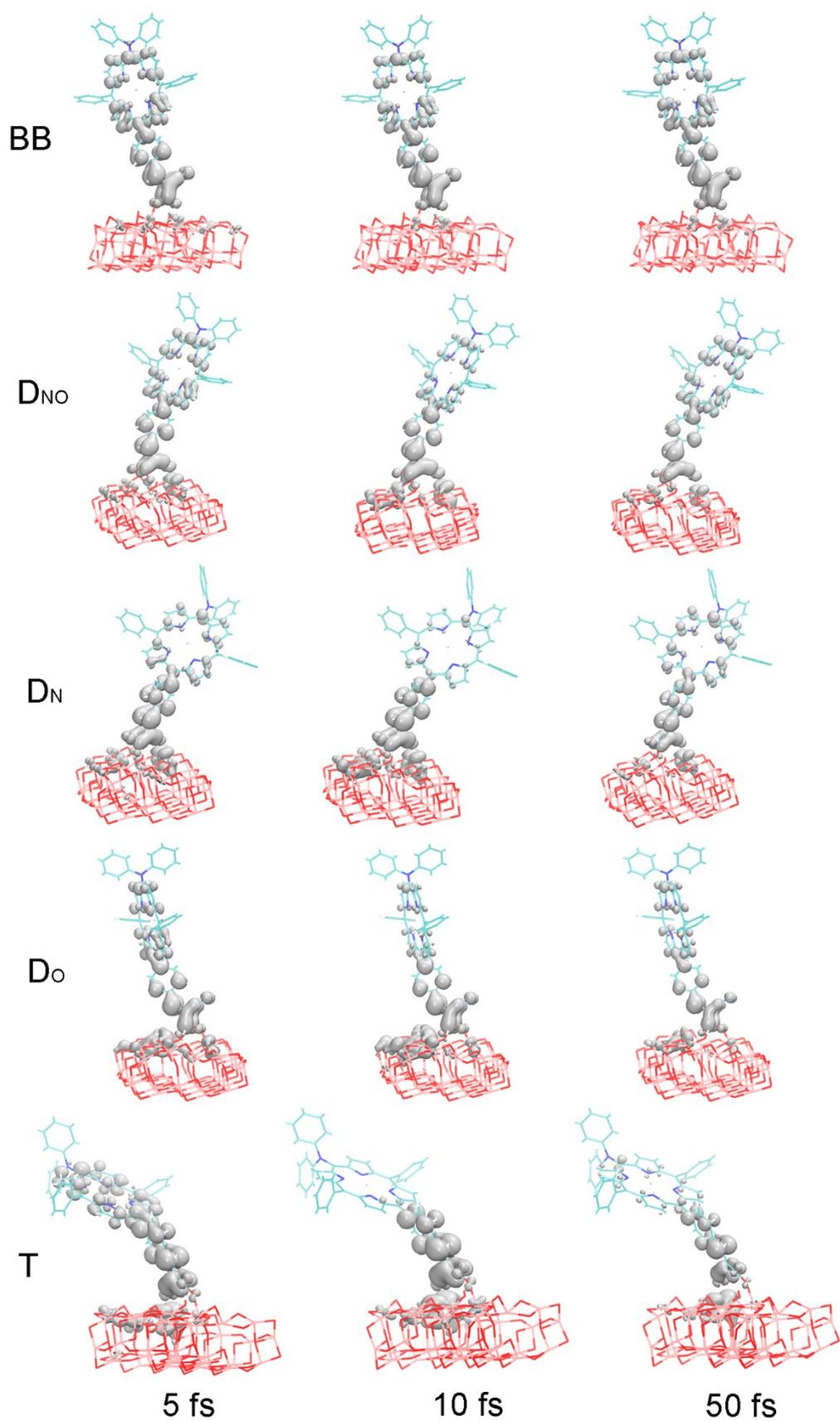


Figure S6. Snapshots of an electronic density isosurface during the evolution of time-dependent charge distribution of T1/TiO₂ system at 5 fs, 10 fs and 50 fs.

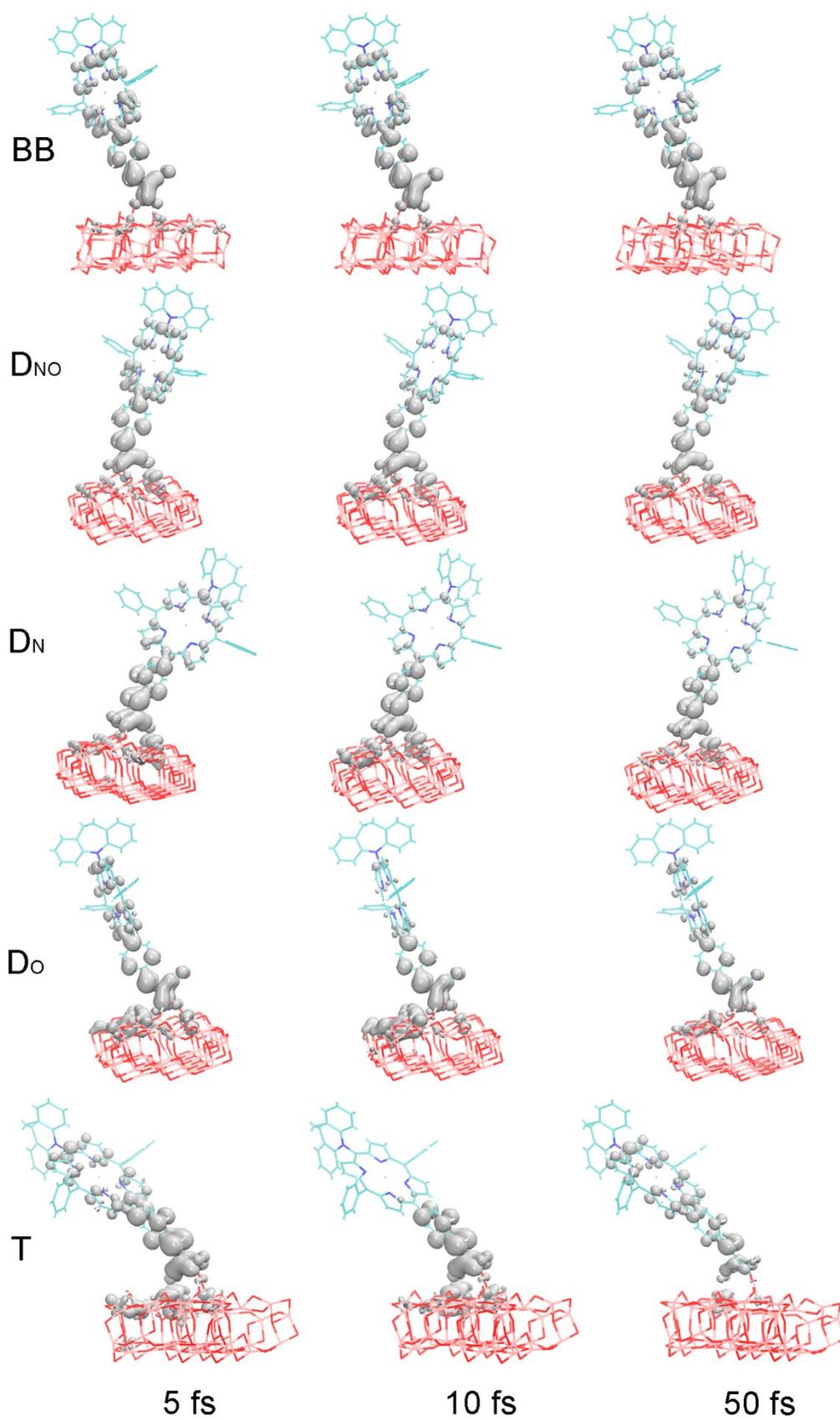


Figure S7. Snapshots of an electronic density isosurface during the evolution of time-dependent charge distribution of T2/TiO₂ system at 5 fs, 10 fs and 50 fs.

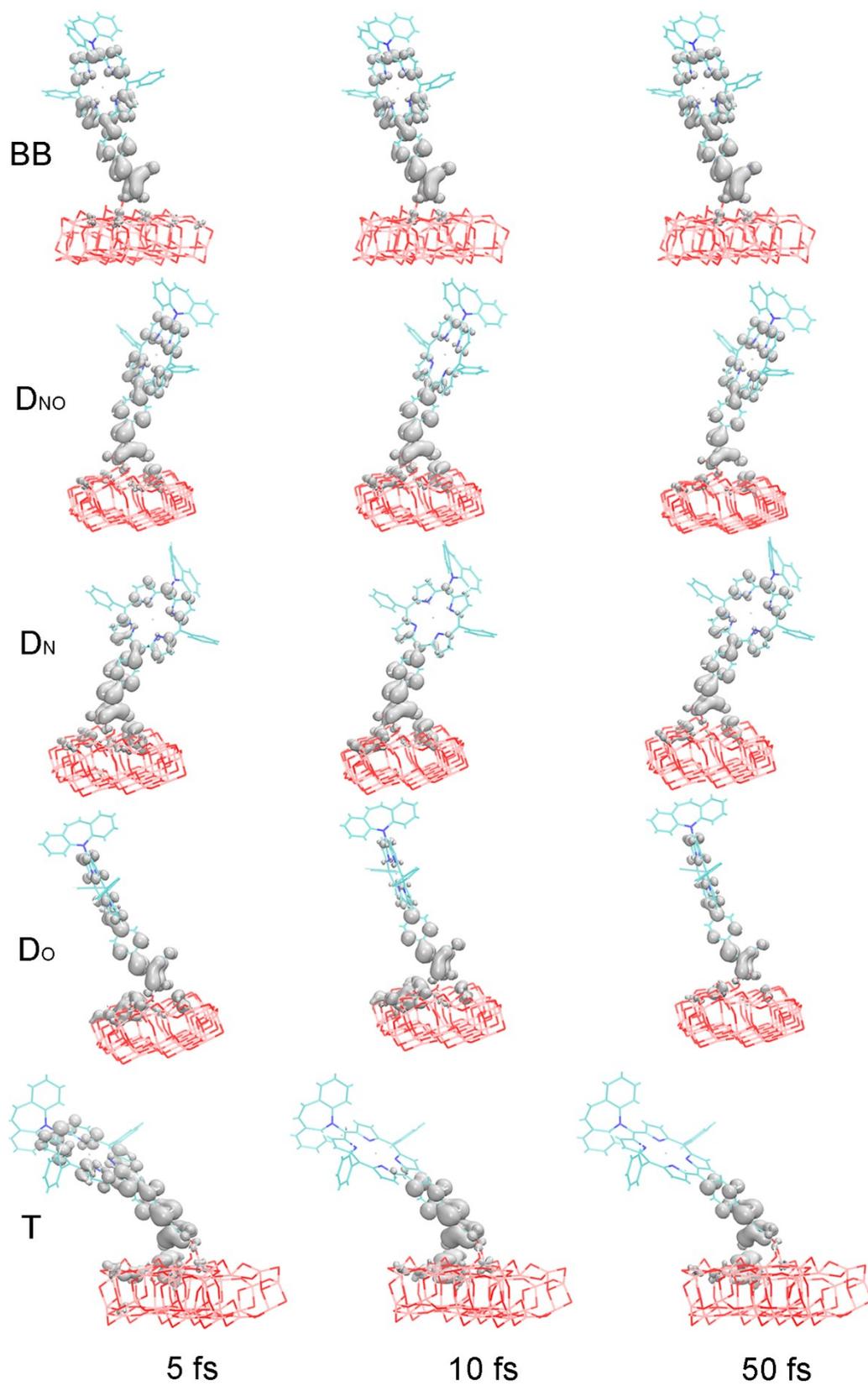


Figure S8. Snapshots of an electronic density isosurface during the evolution of time-dependent charge distribution of T3/TiO₂ system at 5 fs, 10 fs and 50 fs.

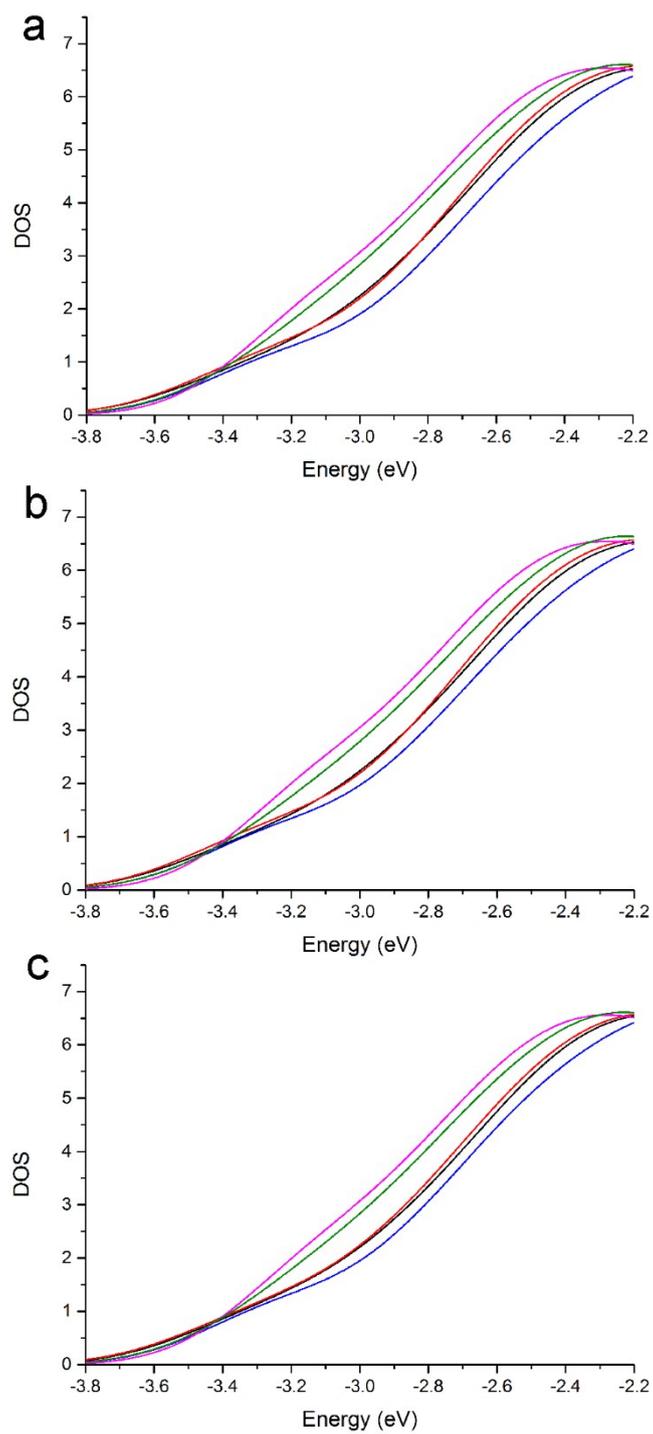


Figure S9 Calculated conduction band PDOS for the TiO₂ of T1 (a), T2 (b) and T3 (c) absorbed on TiO₂ surface with adsorption configurations BB (magenta), T (green), D_N (red), D_{NO} (black), and D_O (blue).

S2. Interfacial Electron Transfer Simulations

The Interfacial Electron Transfer (IET) of dyes on the (TiO₂)₃₈ cluster with ideal and defected anatase (101) surface was investigated with quantum dynamics simulations using the method developed by Rego and Batista,¹⁻⁴ employing the extended Hückel Hamiltonian. IET simulations were performed using IETsim package with a time step of 0.1 fs up to 500 fs on dye/TiO₂ systems. Absorbing potentials were added on the Ti atoms at the bottom layer of TiO₂ to avoid recurrences in electron-transient populations caused by the finite size of the cluster. The brief description of the methodology presented below follows the instruction given by Rego and Batista.¹ The detailed description can be found in ref. 1.

The time-evolved wave function can be written as a linear combination of atomic orbitals (eq 1), where $|i, \alpha\rangle$ refers to the atomic orbital α of atom i .

$$|\Phi(t)\rangle = \sum_{i,\alpha} B_{i,\alpha}(t) |i, \alpha\rangle \quad (1)$$

$B_{i,\alpha}(t)$ in eq 1 is the expansion coefficients, which can be determined according to eq 2 after eq 3 is solved. In eq 3, H and S represent the EH matrix and the overlap matrix respectively in atomic orbital basis set.

$$B_{i,\alpha}(t) = \sum_q Q_{i,\alpha}^q C_q e^{-(i/\hbar)E_q t} \quad (2)$$

$$HQ^q = E_q SQ^q \quad (3)$$

The coefficients C_q in eq 2 are calculated by the initial state expansion in the orthonormal basis set of eigenvectors $|q\rangle$.

$$|\Phi(0)\rangle = \sum_q C_q |q\rangle \quad (4)$$

The coefficients $Q_{i,\alpha}^q$ in eq 2 can be defined according to the expansion of the eigenvectors $|q\rangle$.

$$|q\rangle = \sum_{i,\alpha} Q_{i,\alpha}^q |i, \alpha\rangle \quad (5)$$

To investigate the IET process, we calculate survival probability, $P(t)$, which is defined as the probability that the electron is still localized in the adsorbates at time t after excitation (described in eq 6).

$$P(t) = \left| \sum_{i,\alpha} \sum_{j,\beta}^{MOL} B_{i,\alpha}^*(t) B_{j,\beta}(t) S_{\alpha,\beta}^{i,j} \right| \quad (6)$$

$S_{\alpha,\beta}^{i,j} = \langle i, \alpha | j, \beta \rangle$, where α and β denote specific orbitals in atoms i and j . The sum over j atoms includes all the atoms of dye/TiO₂ system, whereas the sum over i atoms excludes the atoms

of TiO₂ cluster.

The LUMO orbitals of adsorbates were selected as initial states based on TD-DFT calculation. Approximate characteristic IET times were determined from the exponential fitting to the survival probabilities.

REFERENCES

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